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PATENT
Attorney Docket No.: 000939-073311US
Client Ref. No.: P01HA010/US

Assistant Commissioner for Patents
Washington, D.C. 20231

On December 9, 2002

TOWNSEND and TOWNSEND and CREW LLP

By: [Signature]

10/Amst
a
J. Markley
1-6-03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hong Koo Kim

Application No.: 09/747,779

Filed: December 22, 2000

For: FABRICATION METHOD AND
STRUCTURE FOR FERROELECTRIC
NONVOLATILE MEMORY FIELD
EFFECT TRANSISTOR

Examiner: Marcos D. Pizarro Crespo

Art Unit: 2814

AMENDMENT

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Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed September 24, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 25 without prejudice; amend claims 1, 13, 16, and 18-21; and add new claim 26. The remaining claims are unamended, but are reproduced below for the Examiner's convenience and reference.

1. (Amended) A method for fabricating a non-volatile memory device, the method comprising:
- providing a substrate;

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